Title (en)

Semiconductor device comprising conductive layers.

Title (de)

Halbleiteranordnung mit Leiterschichten.

Title (fr)

Dispositif semi-conducteur comprenant des couches conductrices.

Publication

EP 0353414 A2 19900207 (EN)

Application

EP 89109477 A 19890526

Priority

JP 12878088 A 19880526

Abstract (en)

A first conductive layer (2, 12) for transfer of signals faces a second conductive layer (3) for transfer of analog signals, with an insulating film (4) interposed therebetween. A third conductive layer (5) is formed within the insulating film, the third conductive layer being supplied with a fixed potential and facing the first and second conductive layers.

IPC 1-7

H01L 23/522; H01L 23/58

IPC 8 full level

H01L 21/768 (2006.01); **H01L 21/82** (2006.01); **H01L 21/822** (2006.01); **H01L 23/522** (2006.01); **H01L 23/528** (2006.01); **H01L 27/04** (2006.01)

CPC (source: EP KR)

H01L 23/5222 (2013.01 - EP); **H01L 23/5286** (2013.01 - EP); **H01L 27/02** (2013.01 - KR); **H01L 27/04** (2013.01 - KR); H01L 2924/0002 (2013.01 - EP)

C-Set (source: EP)

H01L 2924/0002 + H01L 2924/00

Cited by

EP0735584A3; EP0837503A3; EP0567694A1; EP0473144A3; EP0903783A1; FR2768852A1; US6111742A

Designated contracting state (EPC)

DE FR GB

DOCDB simple family (publication)

EP 0353414 A2 19900207; **EP 0353414 A3 19901031**; JP H01297839 A 19891130; KR 900019220 A 19901224; KR 920008420 B1 19920928

DOCDB simple family (application)

EP 89109477 A 19890526; JP 12878088 A 19880526; KR 890007065 A 19890526